IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-22 (Canceled)

23. (New) A semiconductor device comprising:

a pixel region in which a plurality of thin film transistors are arranged in matrix;

a picture signal supply source for supplying a picture signal;

a switching circuit connected to a source signal line and a plurality of voltage lines for selecting at least one of said voltage lines;

a latch circuit for supplying said picture signal from said picture signal supply source to said switching circuit;

a memory for storing data used in gamma correction of a voltage applied to said at least one of said voltage lines; and

a gamma correction control circuit for adjusting said voltage based on said data to carry out said gamma correction of said voltage,

wherein said plurality of thin film transistors and said memory and said gamma correction control circuit are provided over a same insulating surface.

24. (New) A device according to claim 23 wherein said memory comprises a nonvolatile memory.

25. (New) A device according to claim 23 wherein said picture signal is a digital signal.

26. (New) A device according to claim 23 wherein the picture signal is an analog signal, and the semiconductor device further comprises a conversion circuit for converting said analog signal to a digital signal.

27. (New) A device according to claim 23 wherein an active layer of each of said thin film transistors has a thickness of 10 to 100 nm.

28. (New) A device according to claim 23 wherein said semiconductor device is incorporated into one selected from the group consisting of a video camera, a still camera, a projector, a head mount display, a car navigation system, a personal computer, a portable information terminal, a mobile computer and a portable telephone.

29. (New) A device according to claim 23 further comprising a shift register.

30. (New) A device according to claim 23 wherein said memory comprises a thin film transistor.

31. (New) A device according to claim 23 wherein said gamma correction control circuit comprises a thin film transistor.

32. (New) A semiconductor device comprising:

an electroluminescence element;

a pixel region in which a plurality of thin film transistors are arranged in matrix;

a picture signal supply source for supplying a picture signal;

a switching circuit connected to a source signal line and a plurality of voltage lines for selecting at least one of said voltage lines;

a latch circuit for supplying said picture signal from said picture signal supply source to said switching circuit;

a memory for storing data used in gamma correction of a voltage applied to said at least one of said voltage lines; and

a gamma correction control circuit for adjusting said voltage based on said data to carry out said gamma correction of said voltage,

wherein said plurality of thin film transistors and said memory and said gamma correction control circuit are provided over a same insulating surface.

33. (New) A device according to claim 32 wherein said memory comprises a nonvolatile memory.

34. (New) A device according to claim 32 wherein said picture signal is a digital signal.

35. (New) A device according to claim 32 wherein the picture signal is an analog signal, and the semiconductor device further comprises a conversion circuit for converting said analog signal to a digital signal.

36. (New) A device according to claim 32 wherein an active layer of each of said thin film transistors has a thickness of 10 to 100 nm.

37. (New) A device according to claim 32 wherein said semiconductor device is incorporated into one selected from the group consisting of a video camera, a still camera, a projector, a head mount display, a car navigation system, a personal computer, a portable information terminal, a mobile computer and a portable telephone.

38. (New) A device according to claim 32 further comprising a shift register.

39. (New) A device according to claim 32 wherein said memory comprises a thin film transistor.

40. (New) A device according to claim 32 wherein said gamma correction control circuit comprises a thin film transistor.